**Poly-gate SiO$_2$ = 4.5 nm**

**Nitride = 7.3 nm**

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**Nanowires**

**Floating Gate, $L_g$ = 1 µm**

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**Source**

**Drain**

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**A-A’ cut GAA**

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**Buried Oxide**

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**Weff = (93 nm × 2 + 7 nm × 2) × 10**

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**SiO$_2$ = 4.5 nm**

**Nitride = 7.3 nm**